

Description

The G06N10 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

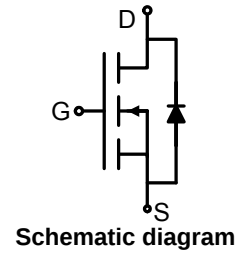
General Features

V_{DS}	$R_{DS(ON)}(Typ)$ @ $V_{GS}=10V$	I_D
100V	195m Ω	6A

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- RoHS Compliant

Application

- Power switching application
- LED lighting

**Ordering Information**

Part Number	Marking	Case	Packaging
G06N10	G06N10	TO-252	2500pcs/Reel

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	6	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	20	A
Maximum Power Dissipation	P_D	25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	6	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	112	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA

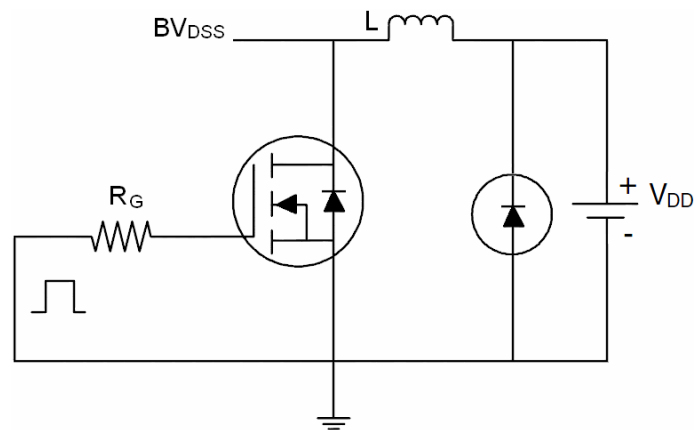
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	2.0	3.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =6A	-	195	240	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =6A	2	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	190	-	PF
Output Capacitance	C _{oss}		-	22	-	PF
Reverse Transfer Capacitance	C _{rss}		-	13	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =6.0A, R _L =39Ω V _{GS} =10V, R _G =1Ω	-	6	-	nS
Turn-on Rise Time	t _r		-	10	-	nS
Turn-Off Delay Time	t _{d(off)}		-	10	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =6.0A, V _{GS} =10V	-	5.2	-	nC
Gate-Source Charge	Q _{gs}		-	0.75	-	nC
Gate-Drain Charge	Q _{gd}		-	1.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =6.0A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	2	A

Notes:

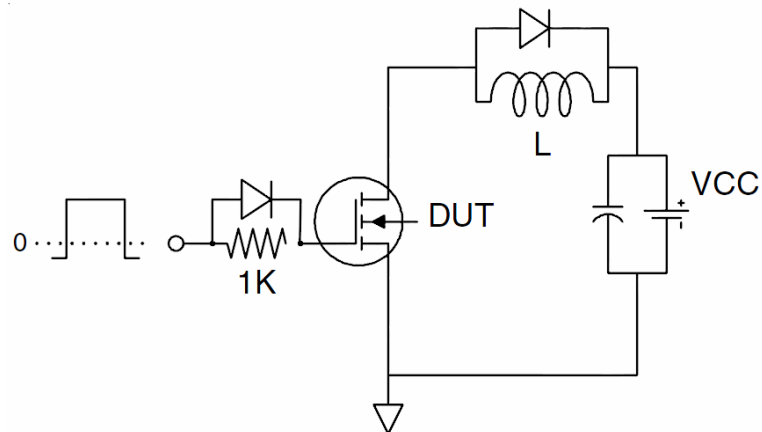
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

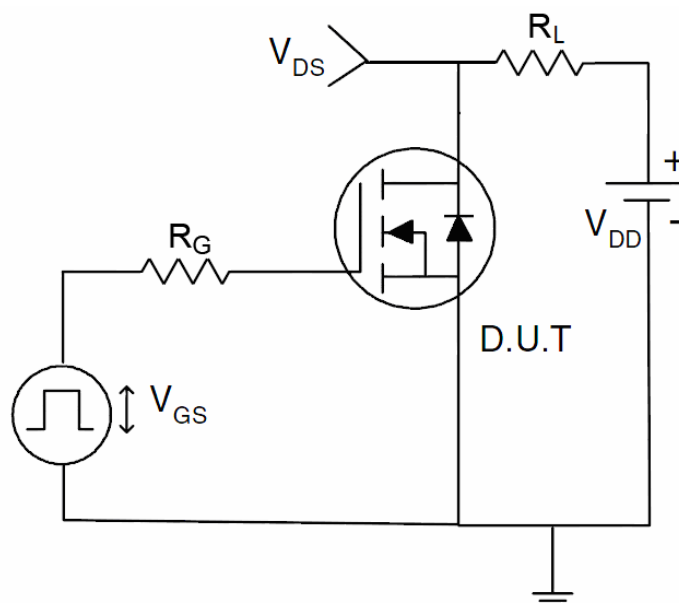
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

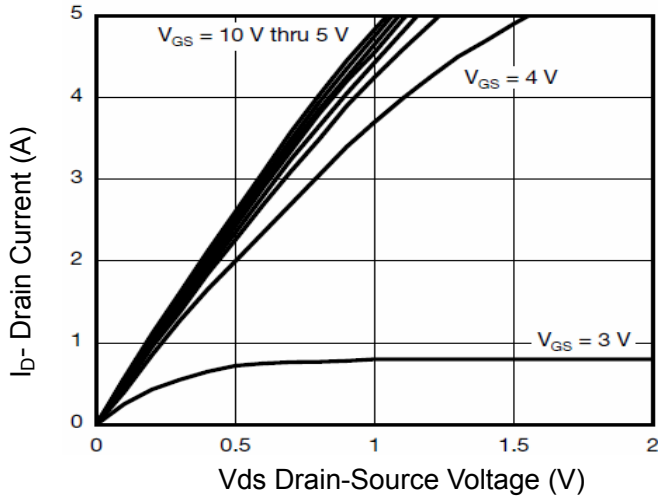


Figure 1 Output Characteristics

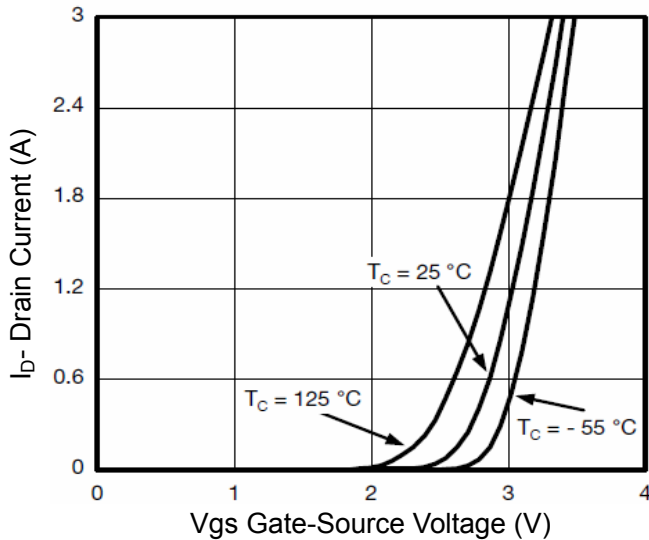


Figure 2 Transfer Characteristics

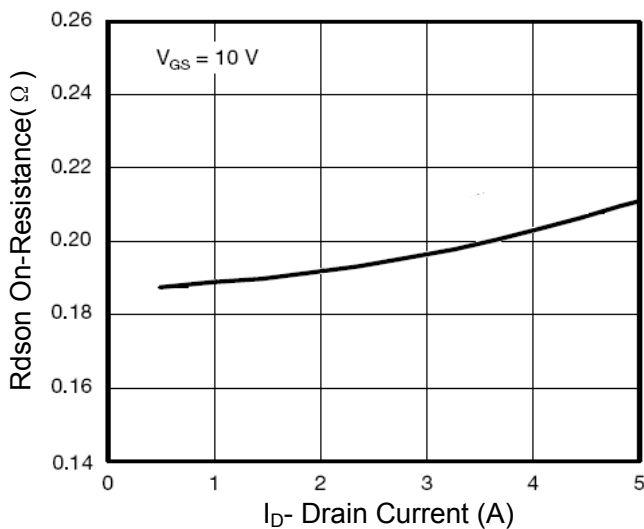


Figure 3 $R_{DS(on)}$ - Drain Current

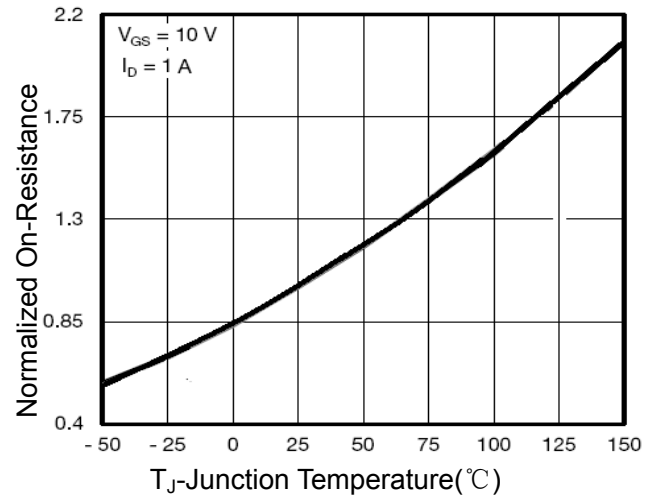


Figure 4 $R_{DS(on)}$ -Junction Temperature

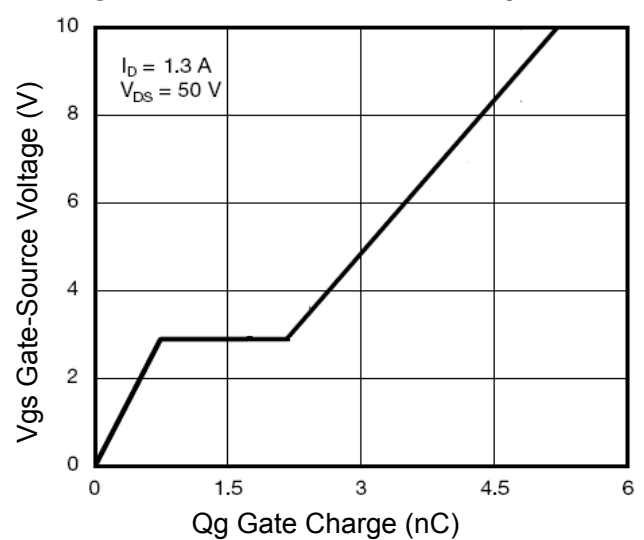


Figure 5 Gate Charge

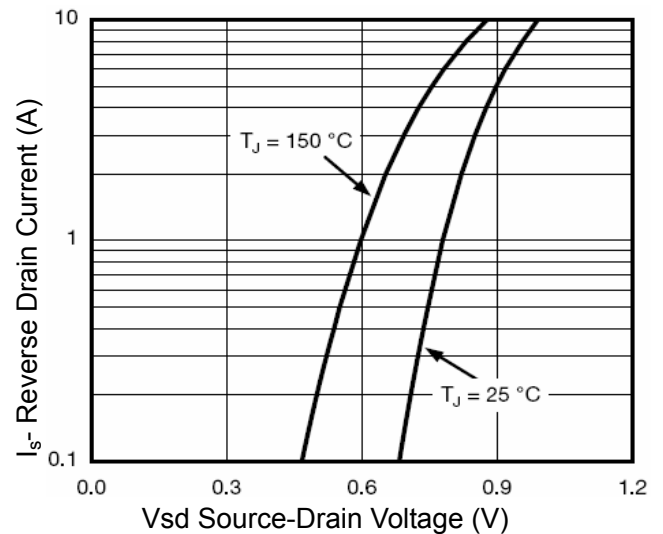


Figure 6 Source- Drain Diode Forward

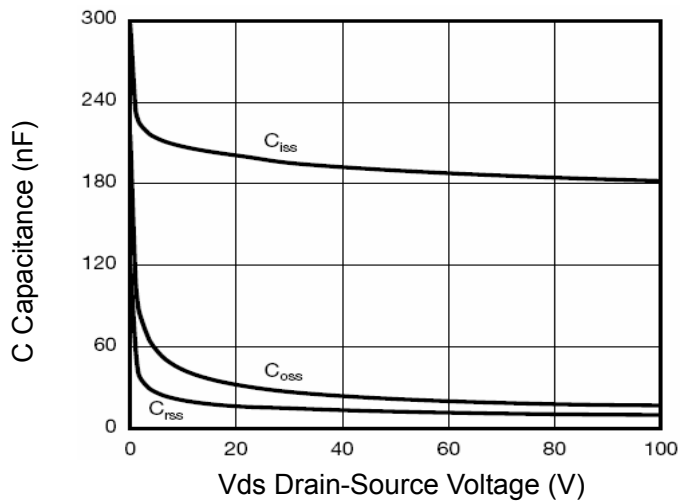


Figure 7 Capacitance vs Vds

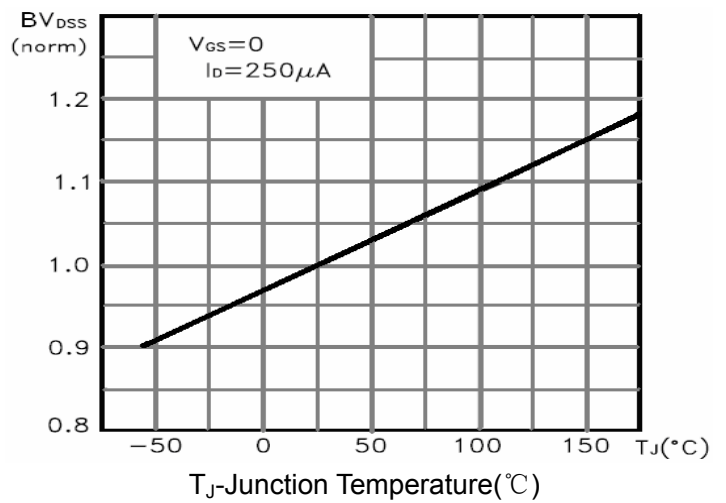


Figure 9 BV_{DSS} vs Junction Temperature

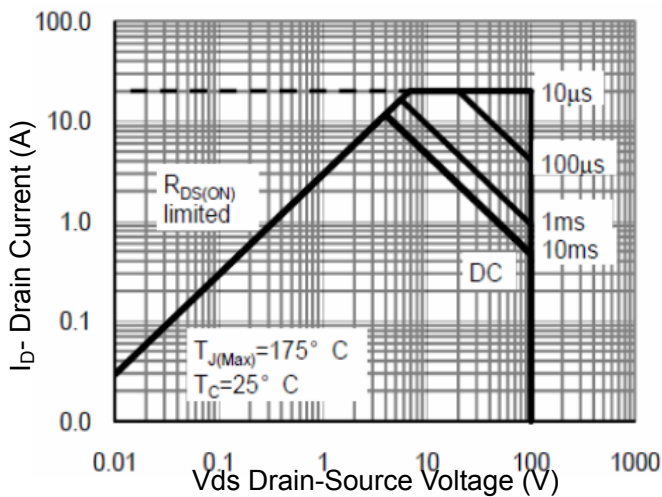


Figure 8 Safe Operation Area

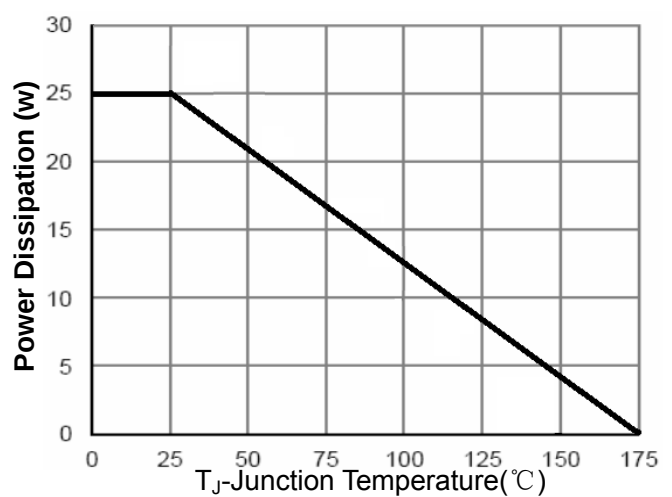


Figure 10 Power De-ratin

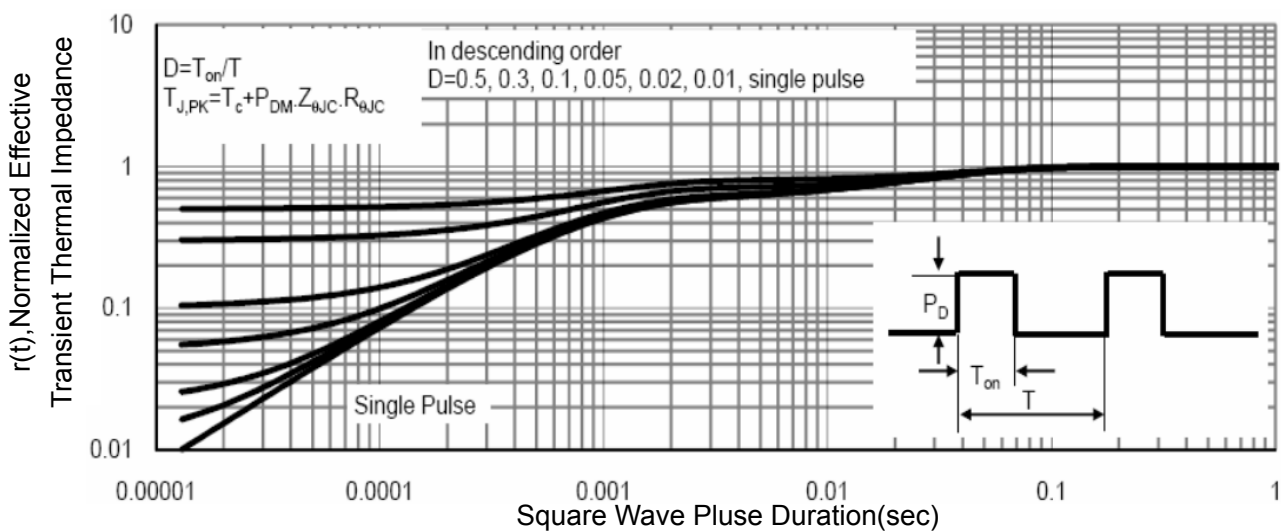
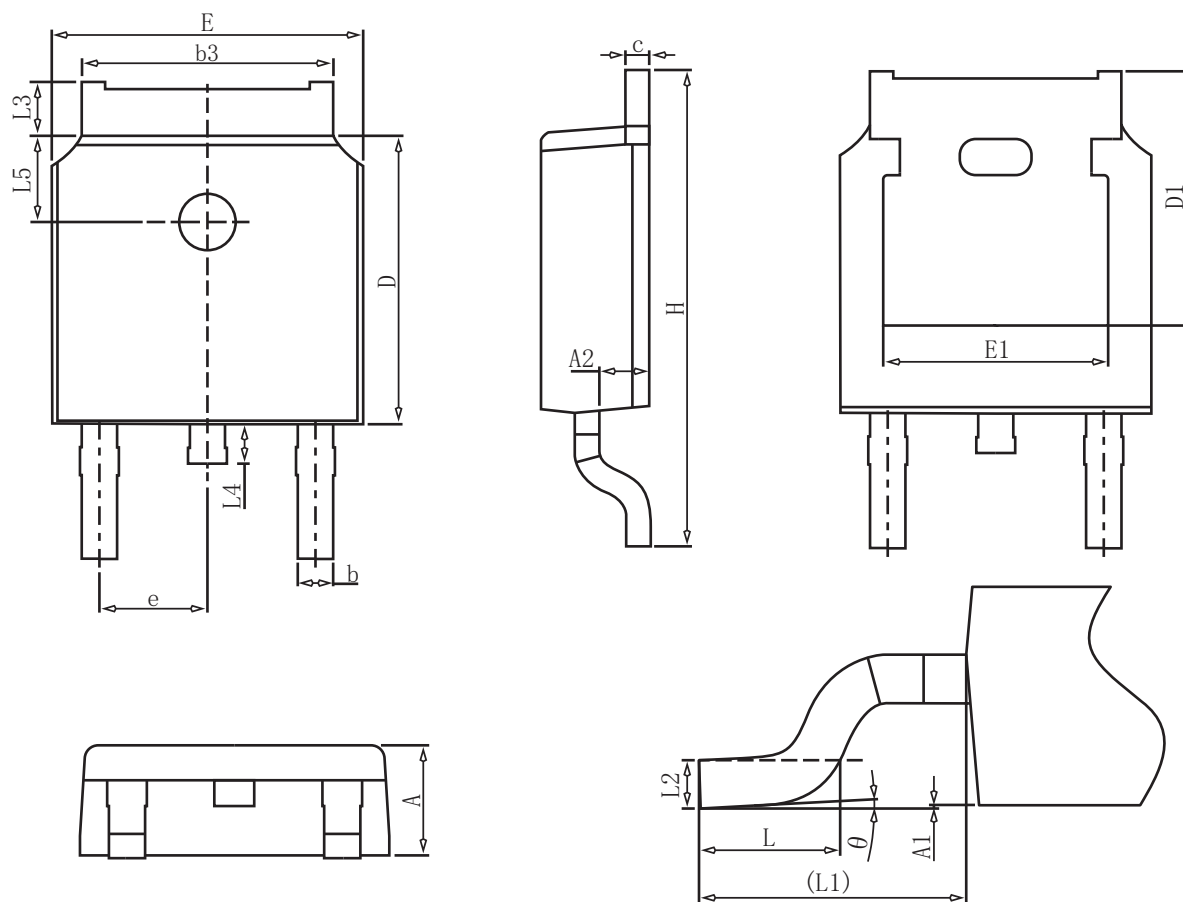


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	—	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	—	—
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	—	1.28
L4	0.50	—	1.00
L5	1.65	1.80	1.95
θ	0°	—	8°